

AC CURRENT GENERATION

Galambos Tamás

2015.11.12.

AC CURRENT

- DC currents
 - Special conditions
 - Time-reversal asymmetry
 - Spatial asymmetry
- AC currents
 - Only condition: scatterer's properties change periodically in time
 - 3 different sources of AC current
 - Scattering: varying redistribution of incoming electrons to outgoing channels
 - Periodical change of charge localized on scatterer
 - Bias between reservoirs
 - Note: even DC bias can result in AC current

ADIABATIC AC CURRENT

- Adiabatic regime: $\varpi = \hbar\Omega_0/\delta E \rightarrow 0$
- Calculate I_α from the Floquet theorem: $I_\alpha(t) = \sum_{l=-\infty}^{\infty} e^{-il\Omega_0 t} I_{\alpha,l}$
- Using the Fourier harmonics:

$$I_{\alpha,l} = \frac{e}{h} \int_0^\infty dE \left\{ \sum_{\beta=1}^{N_r} \sum_{n=-\infty}^{\infty} S_{F,\alpha\beta}^*(E, E_n) S_{F,\alpha\beta}(E_l, E_n) f_\beta(E_n) - \delta_{l0} f_\alpha(E) \right\}$$

- We replace $E_n \rightarrow E$ and $n \rightarrow -n$ in the sums, use first order adiabatic expansion:

$$S_{F,\alpha\beta}(E_n, E) = S_{\alpha\beta,n}(E) + \frac{n\hbar\Omega_0}{2} \frac{\partial S_{\alpha\beta,n}}{\partial E} + \hbar\Omega_0 A_{\alpha\beta,n} + \mathcal{O}(\varpi^2)$$

ADIABATIC AC CURRENT

- Calculate the product:

$$S_{F,\alpha\beta}^*(E_n, E) S_{F,\alpha\beta}(E_{l+n}, E) = S_{\alpha\beta,n}^* S_{\alpha\beta,l+n} + \hbar\Omega_0 \left\{ \frac{n}{2} \frac{\partial S_{\alpha\beta,n}^*}{\partial E} S_{\alpha\beta,l+n} + \frac{(n+l)}{2} \frac{\partial S_{\alpha\beta,n+l}}{\partial E} S_{\alpha\beta,n}^* + (S_{\alpha\beta,n}^* A_{\alpha\beta,l+n} + A_{\alpha\beta,n}^* S_{\alpha\beta,n+l}) \right\} + \mathcal{O}(\varpi^2)$$

- And sum up over n:

$$\sum_{n=-\infty}^{\infty} S_{F,\alpha\beta}^*(E_n, E) S_{F,\alpha\beta}(E_{l+n}, E) = \left(|S_{\alpha\beta}|^2 \right)_l + \frac{i\hbar}{2} \left(-\frac{\partial^2 S_{\alpha\beta}^*}{\partial t \partial E} S_{\alpha\beta} + \frac{\partial^2 S_{\alpha\beta}}{\partial t \partial E} S_{\alpha\beta}^* \right)_l + \hbar\Omega_0 (S_{\alpha\beta}^* A_{\alpha\beta} + A_{\alpha\beta}^* S_{\alpha\beta})_l + \mathcal{O}(\varpi^2)$$

3 PARTS OF CURRENT - 1

- We arrive in the first order approximation in Ω_0 at the 3 mentioned terms:

$$I_\alpha(t) = I_\alpha^{(V)}(t) + I_\alpha^{(Q)}(t) + I_\alpha^{(gen)}(t)$$

- First term:

$$I_\alpha^{(V)}(t) = \frac{e}{h} \int_0^\infty dE \sum_{\beta=1}^{N_r} |S_{\alpha\beta}(t, E)|^2 \{f_\beta(E) - f_\alpha(E)\}$$

- Exists only if there is a difference of chemical potentials or temperatures in reservoirs (“external bias”)

3 PARTS OF CURRENT - 1

- Has to satisfy unitarity condition  Conservation law

$$\sum_{\alpha=1}^{N_r} I_{\alpha}^{(V)}(t) = 0$$

- This is the same as for the DC current
- Conservation law justifies the separation of this term from total current
- Association with the case of non-zero bias between reservoirs ($\Delta T, \Delta\mu, \Delta U, \dots$)

3 PARTS OF CURRENT - 2

- The second term corresponds to the current contribution of the varying charge $Q(t)$ localized on the scatterer

$$I_{\alpha}^{(Q)}(t) = -e \frac{\partial}{\partial t} \int_0^{\infty} dE \sum_{\beta=1}^{N_r} f_{\beta}(E) \frac{dN_{\alpha\beta}(t, E)}{dE}$$

- Where:

$$\frac{dN_{\alpha\beta}(t, E)}{dE} = \frac{i}{4\pi} \left\{ S_{\alpha\beta}(t, E) \frac{\partial S_{\alpha\beta}^*(t, E)}{\partial E} - \frac{\partial S_{\alpha\beta}(t, E)}{\partial E} S_{\alpha\beta}^*(t, E) \right\}$$

- Is the frozen partial Density Of States (DOS), expressed in terms of the frozen scattering matrix elements

3 PARTS OF CURRENT - 2

- Sum up to all leads  Charge conservation law:

$$\sum_{\alpha=1}^{N_r} I_{\alpha}^{(Q)}(t) + \frac{\partial Q(t)}{\partial t} = 0$$

- Where the charge localized on the scatterer is:

$$Q(t) = e \int_0^{\infty} dE \sum_{\alpha=1}^{N_r} \sum_{\beta=1}^{N_r} f_{\beta}(E) \frac{dN_{\alpha\beta}(E, t)}{dE}$$

- Other current components should also figure in the charge conservation, but sum is zero
- Really a current due to variation of scatterer charge

3 PARTS OF CURRENT - 3

- First 2 terms were inherent to stationary scatterer
- Third term only if dynamical scatterer

$$I_{\alpha}^{(gen)}(t) = \int_0^{\infty} dE \sum_{\beta=1}^{N_r} f_{\beta}(E) \frac{dI_{\alpha\beta}(t, E)}{dE}$$

- Partial Spectral Current Density: a flow generated by the dynamical scatterer from lead β to lead α

$$\frac{dI_{\alpha\beta}}{dE} = \frac{e}{h} \left(2\hbar\Omega_0 \text{Re} [S_{\alpha\beta}^* A_{\alpha\beta}] + \frac{1}{2} P \{ S_{\alpha\beta}, S_{\alpha\beta}^* \} \right)$$

3 PARTS OF CURRENT - 3

- Conservation law

$$\sum_{\alpha=1}^{N_r} I_{\alpha}^{(gen)}(t) = 0 \quad \leftarrow \quad \sum_{\alpha=1}^{N_r} \frac{dI_{\alpha\beta}(t, E)}{dE} = 0$$

- No internal source of charge, only redistribution
- Spectral Current Density (sum up for all β leads):

$$\frac{dI_{\alpha}}{dE} = \frac{e}{h} P \{ \hat{S}, \hat{S}^{\dagger} \}_{\alpha\alpha}$$

- Generated current \longleftrightarrow Anomalous scattering matrix (violation of scattering direction reversal symmetry)

EXTERNAL AC BIAS INTRO


- Current flowing through the dynamical scatterer due to reservoirs biased with periodic in time potentials

$$V_{\alpha\beta}(t) = V_{\alpha\beta}(t + \mathcal{T}) \equiv V_{\alpha}(t) - V_{\beta}(t)$$

- Generated current interferes with bias induced current, Interference Current contribution
- Let the reservoir potentials vary with same frequency as the parameters of the scatterer

$$V_{\alpha}(t) = V_{\alpha} \cos(\Omega_0 t + \phi_{\alpha}), \quad \alpha = 1, \dots, N_r$$

EXTERNAL AC BIAS INTRO

- Phase-coherent transport phenomena  Spatially uniform potentials of electron reservoirs, appears as phase in the incident electron wavefunctions
- Suppose constant μ , independent of potentials
- Schrödinger equation with spatially uniform potential can be integrated

$$i\hbar \frac{\partial \Psi_\alpha}{\partial t} = H_{0,\alpha} \Psi_\alpha + eV_\alpha(t) \Psi_\alpha$$

$$\Psi_\alpha = \Psi_{0,\alpha} e^{-i\hbar^{-1} \int_{-\infty}^t dt' eV_\alpha(t')}$$

$$\Psi_{0E,\alpha} = e^{-i\frac{E}{\hbar}t} \psi_{E,\alpha}(\vec{r})$$

EXTERNAL AC BIAS INTRO

- With the above defined potential, solution with E energy ($eV_\alpha > 0$):

$$\Psi_{E,\alpha} = e^{-i\frac{E}{\hbar}t} \bar{\psi}_{E,\alpha}(\vec{r}) \sum_{n=-\infty}^{\infty} e^{-in\phi_\alpha} J_n\left(\frac{eV_\alpha}{\hbar\Omega_0}\right) e^{-in\Omega_0 t}$$

- Where we used:

$$e^{-iX \sin(\Omega_0 t + \phi_\alpha)} = \sum_{n=-\infty}^{\infty} J_n(X) e^{-in(\Omega_0 t + \phi_\alpha)}$$

$$C = e^{ieV_\alpha/(\hbar\Omega_0) \sin(\Omega_0 t' + \phi_\alpha)}|_{t'=-\infty}$$

$$\bar{\psi}_{E,\alpha}(\vec{r}) = C\psi_{E,\alpha}(\vec{r})$$

- This is a Floquet-type wave function, spatial part only depends on E, but not on sub-band number n

EXTERNAL AC BIAS INTRO

- Therefore Floquet wave function is normalized as stationary wave function

$$\int d^3 r |\Psi_{E,\alpha}|^2 = \int d^3 r |\psi_{E,\alpha}|^2$$

- Proof: $\sum_{n=-\infty}^{\infty} J_n(X) J_{n+q}(X) = \delta_{q0}$ using $X = eV_\alpha/(\hbar\Omega_0)$
 $q = m - n$
 $|C|^2 = 1$

$$\begin{aligned} |\Psi_{E,\alpha}|^2 &= |\psi_{E,\alpha}|^2 \sum_{n=-\infty}^{\infty} \sum_{m=-\infty}^{\infty} e^{-i(n-m)\phi_\alpha} e^{-i(n-m)\Omega_0 t} J_n(X) J_m(X) \\ &= |\psi_{E,\alpha}|^2 \sum_{q=-\infty}^{\infty} e^{iq\phi_\alpha} e^{iq\Omega_0 t} \sum_{n=-\infty}^{\infty} J_n(X) J_{n+q}(X) = |\psi_{E,\alpha}|^2 \end{aligned}$$

EXTERNAL AC BIAS INTRO

- The Floquet state with energy E in lead a can be occupied by only one electron
- Its measured energy can be any of $E_n = E + n\hbar\Omega_0$ Floquet energies with probability $J_n^2(eV_\alpha/\hbar\Omega_0)$ (square amplitude)
- Mean energy is the energy of the stationary state

$$E [\Psi_{E,\alpha}] = \sum_{n=-\infty}^{\infty} E_n J_n^2 = E \sum_{n=-\infty}^{\infty} J_n^2 + \hbar\Omega_0 \sum_{n=1}^{\infty} n (J_n^2 - J_{-n}^2) = E$$

- Corresponding Fermi distribution only depends on Floquet energy



THANK YOU FOR
YOUR ATTENTION!